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| FORM O-1449 (Modified) | | | Attorney Docket No.: 108-18.1 | | Application No.: 10/777,560 | |
| LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary) | | | Applicant: Harry S. Luan, et al. | | Group: | |
| Filing Date: February 11, 2004 | | | | | | |
| Reference Designation | | | U.S. PATENT DOCUMENTS | | | Page 1 |
| Examiner Initial | Document No. | Date | Name | Class | Sub-class | Filing Date (If Appropriate) |
| FN AA | 6,204,139 | 3/20/01 | Liu et al | 438 | 385 | — |
| FN AB | 6,531,371 | 3/11/03 | Hsu et al | 438 | 385 | — |
| AC | | | | | | |
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| OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.) | | | | | | |
| FN AP | Zhuang et al., "Novell Colossal Magnetoresistive Thin Film Nonvolatile Resistance Random Access Memory (RRAM)," IEEE 2002. | | | | | |
| FN AQ | Liu et al., "A New Concept for Non-Volatile Memory: The Electric Pulse Induced Resistive Change Effect in Colossal Magnetoresistive Thin Films," | | | | | |
| FN AR | Liu et al., "Electric-pulse-induced reversible resistance change effect in magnetoresistive films," American Institute of Physics, 2000, pg. 2749-2751. | | | | | |
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| EXAMINER | DATE CONSIDERED | | | 3/26/2006 | | |

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.